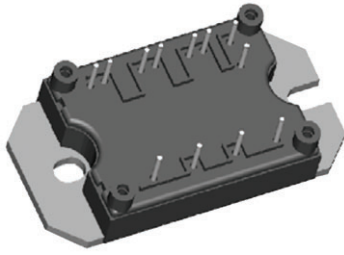



“Half Bridge” IGBT MTP (Warp Speed IGBT), 114 A


MTP

FEATURES

- Gen 4 warp speed IGBT technology
- HEXFRED® antiparallel diodes with ultrasoft reverse recovery
- Very low conduction and switching losses
- Optional SMD thermistor (NTC)
- Very low junction to case thermal resistance
- UL approved file E78996 
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


**RoHS
COMPLIANT**

PRIMARY CHARACTERISTICS	
V_{CES}	600 V
$V_{CE(on)}$ typical at $V_{GE} = 15$ V	2.3 V
I_C at $T_C = 25$ °C	114 A
Speed	30 kHz to 100 kHz
Package	MTP
Circuit configuration	Half bridge

BENEFITS

- Optimized for welding, UPS and SMPS applications
- Low EMI, requires less snubbing
- Direct mounting to heatsink
- PCB solderable terminals
- Very low stray inductance design for high speed operation

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current	I_C	$T_C = 25$ °C	114	A
		$T_C = 109$ °C	50	
Pulsed collector current	I_{CM}		350	
Peak switching current	I_{LM}		350	
Diode continuous forward current	I_F	$T_C = 109$ °C	34	
Peak diode forward current	I_{FM}		200	
Gate to emitter voltage	V_{GE}		± 20	
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	
Maximum power dissipation	P_D	$T_C = 25$ °C	658	W
		$T_C = 100$ °C	263	

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0$ V, $I_C = 500$ μ A	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15$ V, $I_C = 50$ A	-	2.3	3.15	V
		$V_{GE} = 15$ V, $I_C = 100$ A	-	2.5	3.2	
		$V_{GE} = 15$ V, $I_C = 50$ A, $T_J = 150$ °C	-	1.72	2.17	
Gate threshold voltage	$V_{GE(th)}$	$I_C = 0.5$ mA	3	-	6	
Collector to emitter leaking current	I_{CES}	$V_{GE} = 0$ V, $I_C = 600$ A	-	-	0.4	mA
		$V_{GE} = 0$ V, $I_C = 600$ A, $T_J = 150$ °C	-	-	10	
Diode forward voltage drop	V_{FM}	$I_F = 50$ A, $V_{GE} = 0$ V	-	1.58	1.80	V
		$I_F = 50$ A, $V_{GE} = 0$ V, $T_J = 150$ °C	-	1.49	1.68	
		$I_F = 100$ A, $V_{GE} = 0$ V, $T_J = 25$ °C	-	1.9	2.17	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20$ V	-	-	± 250	nA



SWITCHING CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q _g	I _C = 52 A V _{CC} = 400 V V _{GE} = 15 V	-	331	385	nC
Gate to emitter charge (turn-on)	Q _{ge}		-	44	52	
Gate to collector charge (turn-on)	Q _{gc}		-	133	176	
Turn-on switching loss	E _{on}	Internal gate resistors (see electrical diagram) I _C = 50 A, V _{CC} = 480 V, V _{GE} = 15 V, L = 200 μH energy losses include tail and diode reverse recovery, T _J = 25 °C	-	0.26	-	mJ
Turn-off switching loss	E _{off}		-	1.2	-	
Total switching loss	E _{ts}		-	1.46	-	
Turn-on switching loss	E _{on}	Internal gate resistors (see electrical diagram) I _C = 50 A, V _{CC} = 480 V, V _{GE} = 15 V, L = 200 μH energy losses include tail and diode reverse recovery, T _J = 150 °C	-	0.73	-	mJ
Turn-off switching loss	E _{off}		-	1.66	-	
Total switching loss	E _{ts}		-	2.39	-	
Input capacitance	C _{ies}	V _{GE} = 0 V V _{CC} = 30 V f = 1.0 MHz	-	7100	-	pF
Output capacitance	C _{oes}		-	510	-	
Reverse transfer capacitance	C _{res}		-	140	-	
Diode reverse recovery time	t _{rr}	V _{CC} = 200 V, I _C = 50 A dI/dt = 200 A/μs	-	82	97	ns
Diode peak reverse current	I _{rr}		-	8.3	10.6	A
Diode recovery charge	Q _{rr}		-	340	514	nC
Diode reverse recovery time	t _{rr}	V _{CC} = 200 V, I _C = 50 A dI/dt = 200 A/μs T _J = 125 °C	-	137	153	ns
Diode peak reverse current	I _{rr}		-	12.7	14.8	A
Diode recovery charge	Q _{rr}		-	870	1132	nC

THERMISTOR SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Resistance	R ₀ ⁽¹⁾	T ₀ = 25 °C	-	30	-	kΩ
Sensitivity index of the thermistor material	β ⁽¹⁾⁽²⁾	T ₀ = 25 °C T ₁ = 85 °C	-	4000	-	K

Notes

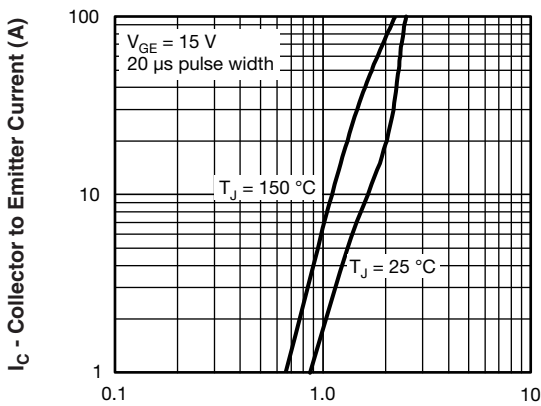
(1) T₀, T₁ are thermistor's temperatures

(2) $\frac{R_0}{R_1} = \exp\left[\beta\left(\frac{1}{T_0} - \frac{1}{T_1}\right)\right]$, temperature in Kelvin

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	IGBT, diode Thermistor	T _J	-40	-	150	°C
			-40	-	125	
Storage temperature range	T _{Stg}		-40	-	125	
Junction to case	IGBT Diode	R _{thJC}	-	-	0.38	°C/W
			-	-	0.8	
Case to sink per module	R _{thCS}	Heatsink compound thermal conductivity = 1 W/mK	-	0.06	-	
Clearance ⁽¹⁾		External shortest distance in air between 2 terminals	5.5	-	-	
Creepage ⁽¹⁾		Shortest distance along the external surface of the insulating material between 2 terminals	8	-	-	mm
Mounting torque to heatsink		A mounting compound is recommended and the torque should be checked after 3 hours to allow for the spread of the compound. Lubricated threads.	3 ± 10 %			Nm
Weight			66			g

Note

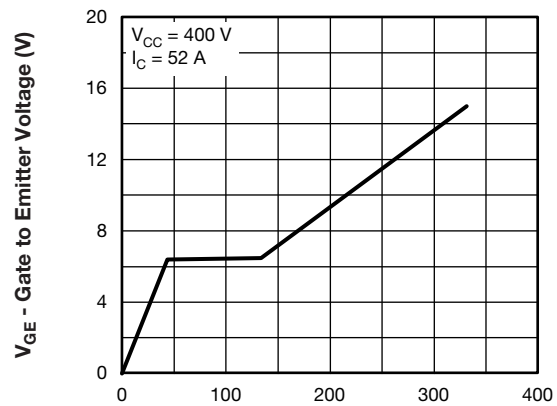
(1) Standard version only i.e. without optional thermistor



94468_01

V_{CE} - Collector to Emitter Voltage (V)

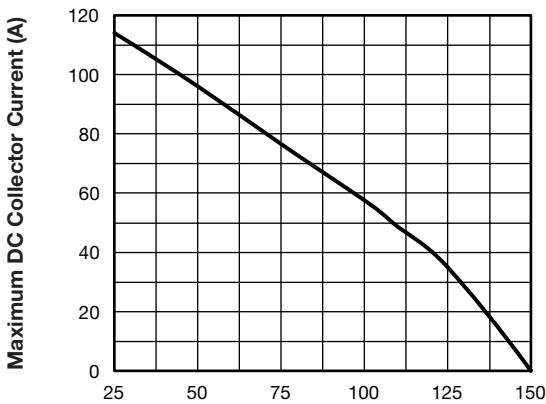
Fig. 1 - Typical Output Characteristics



94468_04

Q_G - Typical Gate Charge (nC)

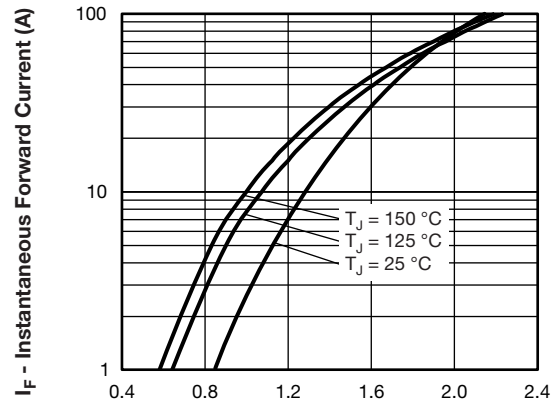
Fig. 4 - Typical Gate Charge vs. Gate to Emitter Voltage



94468_02

T_C - Case Temperature (°C)

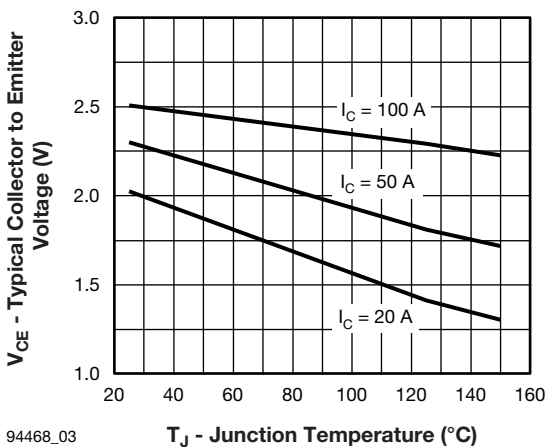
Fig. 2 - Maximum Collector Current vs. Case Temperature



94468_05

V_{FM} - Forward Voltage Drop (V)

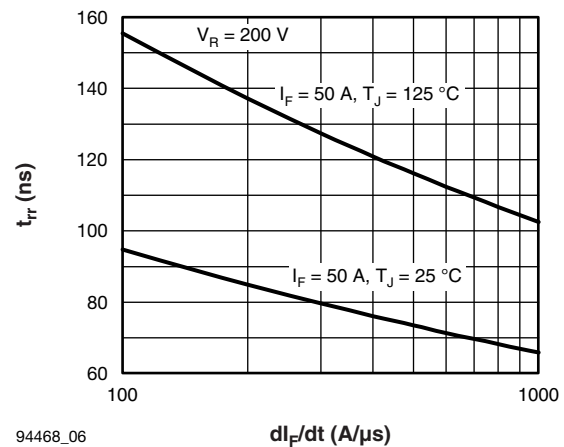
Fig. 5 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current



94468_03

T_J - Junction Temperature (°C)

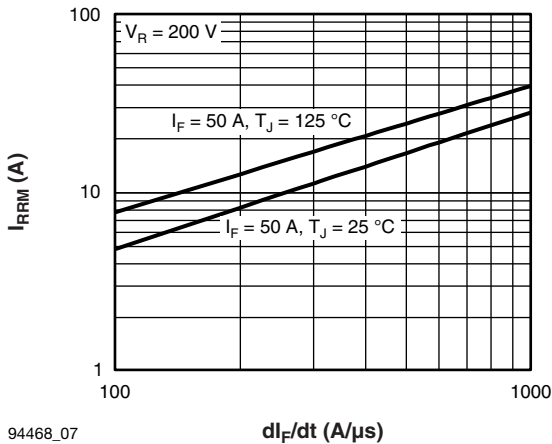
Fig. 3 - Typical Collector to Emitter Voltage vs. Junction Temperature



94468_06

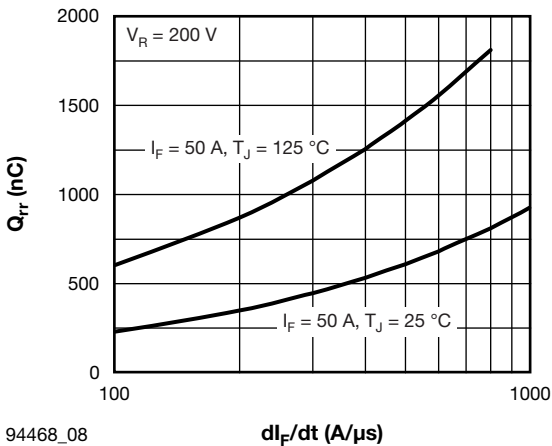
di_F/dt (A/μs)

Fig. 6 - Typical Reverse Recovery Time vs. di_F/dt



94468_07

Fig. 7 - Typical Reverse Recovery Current vs. di_F/dt



94468_08

Fig. 8 - Typical Stored Charge vs. di_F/dt

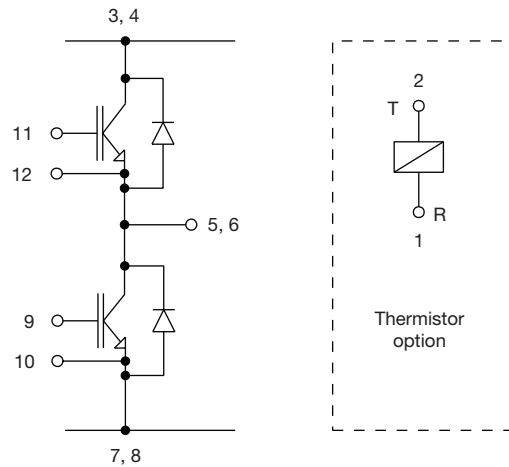


Fig. 9 - Functional Diagram

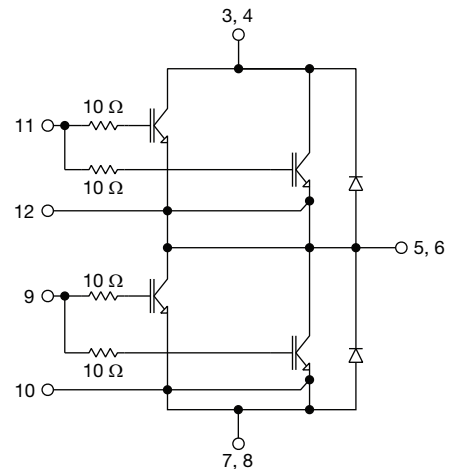


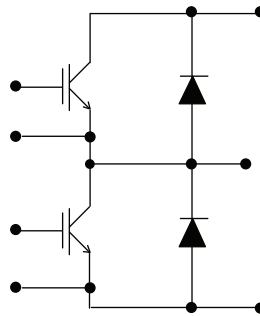
Fig. 10 - Electrical Diagram

ORDERING INFORMATION TABLE

Device code	VS-	50	MT	060	W	H	T	A	PbF
	1	2	3	4	5	6	7	8	9
1	-	Vishay Semiconductors product							
2	-	Current rating (50 = 50 A)							
3	-	Essential part number							
4	-	Voltage rating (060 = 600 V)							
5	-	Speed / type (W = warp IGBT)							
6	-	Circuit configuration (H = half bridge)							
7	-	T = thermistor							
8	-	A = Al ₂ O ₃ substrate							
9	-	Lead (Pb)-free							



CIRCUIT CONFIGURATION



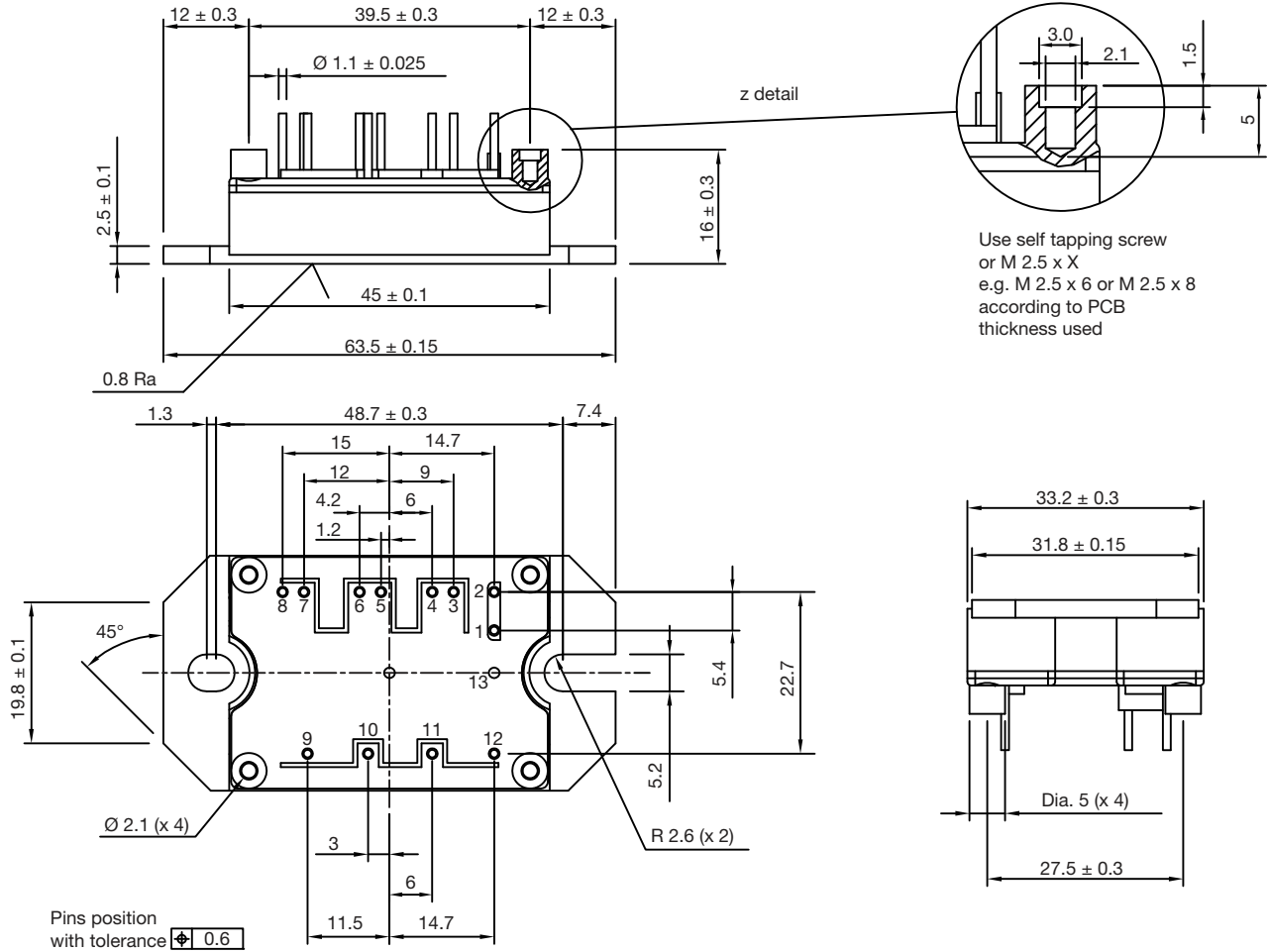
LINKS TO RELATED DOCUMENTS

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95175



MTP

DIMENSIONS in millimeters



Use self tapping screw or M 2.5 x X e.g. M 2.5 x 6 or M 2.5 x 8 according to PCB thickness used

Note

- Unused terminals are not assembled in the package



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